

Amendments to the Specification

Please amend the Abstract as shown.

~~The invention describes a semiconductor component, which is arranged in a semiconductor body, with at least one source zone and with at least one drain zone of in each case a first conductivity type, with at least one body zone of a second conductivity type arranged in each case between source zone and drain zone, and with at least one gate electrode insulated relative to the semiconductor body by means of an insulating layer, the insulating layer being a consolidated, preferably sintered, layer containing quantum dots.~~

~~The invention further describes a method of producing such a semiconductor component.~~

Fig. 1

According to an example embodiment there is a semiconductor component, which is arranged in a semiconductor body, with at least one source zone and with at least one drain zone which in each case is a first conductivity type, with at least one body zone of a second conductivity type arranged in each case between source zone and drain zone, and with at least one gate electrode insulated with an insulating layer relative to the semiconductor body. The insulating layer is a consolidated, preferably sintered, layer containing quantum dots.